

IN THE CLAIMS

1. (currently amended) A heat treatment jig for a semiconductor substrate that is mounted on a heat treatment boat of a vertical heat treatment furnace, comprising:

a semiconductor substrate that is heat treated;

a first jig that is constituted of a silicon material and comes into direct contact with the semiconductor substrate to support; and

a second jig (holder) that holds the first jig and is mounted on the heat treatment boat, wherein the first jig is placed on the second [[jug]] jig so that the first jig is movable relative to the second jig on the surface of the second jig.

2. (previously presented) The heat treatment jig for a semiconductor substrate according to Claim 1:

wherein the first jig has, in a region that comes into direct contact with the semiconductor substrate, a thickness in the range of from 0.5 to 10 mm, the surface roughness in the range of from 0.02 to 10 μm and the flatness of 100 μm or less; and

the second jig has, in a region that comes into direct contact with the first jig, a thickness in the range of from 0.5 to 10 mm, the surface roughness in the range of from 0.02 to 10 μm and the flatness of 200 μm or less.

3. (previously presented) The heat treatment jig for a semiconductor substrate according to Claim 1:

wherein the first jig is 0.5 mm or more in a width that comes into direct contact with the semiconductor substrate.

4. (previously presented) The heat treatment jig for a semiconductor substrate according to Claim 2:

wherein the first jig is 0.5 mm or more in a width that comes into direct contact with the semiconductor substrate.

5. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 1:

wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

6. canceled

7. canceled

8. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 2:
wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

9. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 3:
wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.

10. (withdrawn) A heat treatment jig for a semiconductor substrate according to Claim 4:
wherein in the first jig, on a surface of a region that comes into direct contact with the semiconductor substrate, any one of a silicon carbide film, an oxide film or a poly-silicon film is formed.